# **TRIACS** Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 15 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt 250 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating di/dt 9.0 A/ms minimum at 125°C

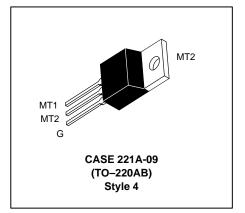
\*Motorola preferred devices

MAC15

SERIES\*







#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

	Parameter		Value	Unit
	k Repetitive Off-State Voltage (1) 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	MAC15M MAC15N	600 800	Volts
	State RMS Current (60 Hz, T <sub>C</sub> = 80°C)		15	A
	k Non-repetitive Surge Current one Full Cycle, 60 Hz, TJ = 125°C)		150	A
Circu	uit Fusing Consideration (t = 8.3 ms)		93	A <sup>2</sup> sec
Peak	k Gate Power (Pulse Width $\leq$ 1.0 µs, T <sub>C</sub> = 80°C)		20	Watts
Aver	rage Gate Power (t = 8.3 ms, T <sub>C</sub> = 80°C)		0.5	Watts
Oper	rating Junction Temperature Range		-40 to +125	°C
Stora	age Temperature Range		-40 to +150	°C
	age Temperature Range ERISTICS		-	-40 to +150

R <sub>θ</sub> JC	Thermal Resistance — Junction to Case	2.0	°C/W
R <sub>θ</sub> JA	— Junction to Ambient	62.5	
тլ	Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	260	°C

(1) V<sub>DRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Preferred devices are Motorola recommended choices for future use and best overall value.



**ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> =  $25^{\circ}$ C unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
IDRM	Peak Repetitive Blocking Current $(V_D = Rated V_{DRM}, Gate Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$			0.01 2.0	mA

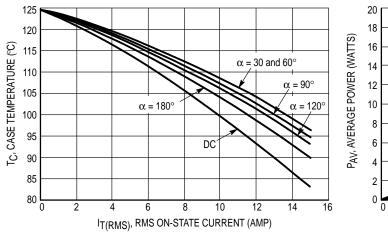
## **ON CHARACTERISTICS**

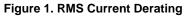
VTM	Peak On-State Voltage* ( $I_{TM} = \pm 21 \text{ A Peak}$ )	_	1.2	1.6	Volts
IGT	Continuous Gate Trigger Current ( $V_D = 12 V, R_L = 100 \Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	5.0 5.0 5.0	13 16 18	35 35 35	mA
Ч	Hold Current ( $V_D = 12 V$ , Gate Open, Initiating Current = ±150 mA)	_	20	40	mA
IL.	Latch Current ( $V_D = 24 \text{ V}, I_G = 35 \text{ mA}$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		33 36 33	50 80 50	mA
V <sub>GT</sub>	Gate Trigger Voltage (V <sub>D</sub> = 12 V, R <sub>L</sub> = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	0.5 0.5 0.5	0.75 0.72 0.82	1.5 1.5 1.5	Volts

#### **DYNAMIC CHARACTERISTICS**

(di/dt) <sub>C</sub>	$ \begin{array}{ll} \mbox{Rate of Change of Commutating Current}^* \mbox{ See Figure 10.} \\ (V_D = 400 \mbox{ V, } I_{TM} = 6.0 \mbox{ A, Commutating dv/dt} = 24 \mbox{ V/}\mu\mbox{s,} & C_L = 10 \mu\mbox{F} \\ \mbox{Gate Open, } T_J = 125^\circ\mbox{C, } f = 250 \mbox{ Hz, No Snubber)} & L_L = 40 \mbox{ mH} \end{array} $	9.0	_	—	A/ms
dv/dt	Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, Gate Open, T <sub>J</sub> = 125°C)	250	_	—	V/µs

\*Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.





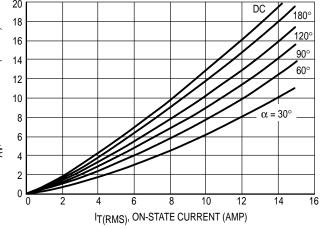
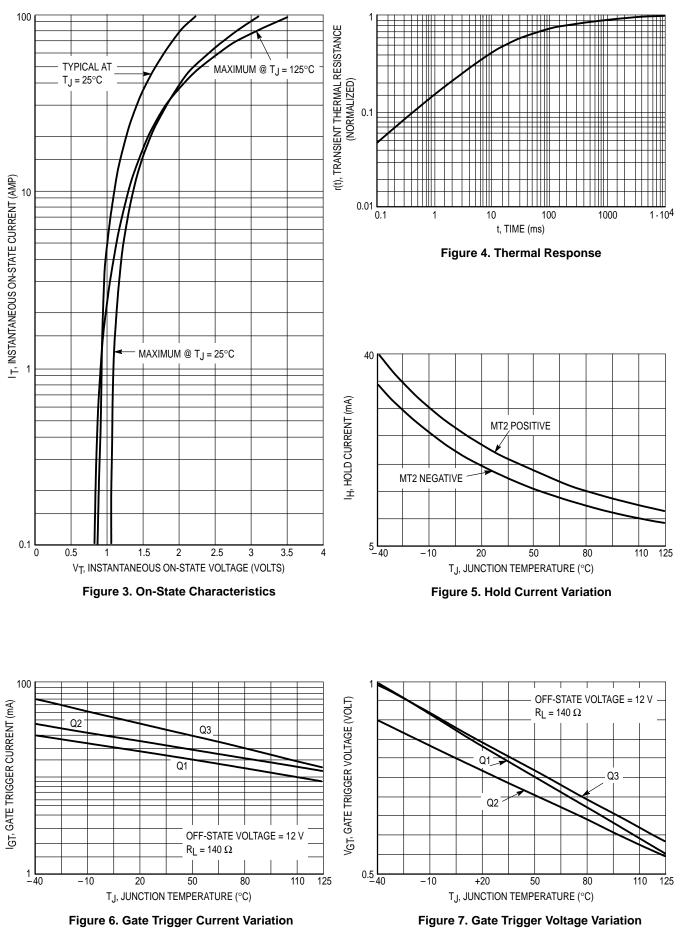
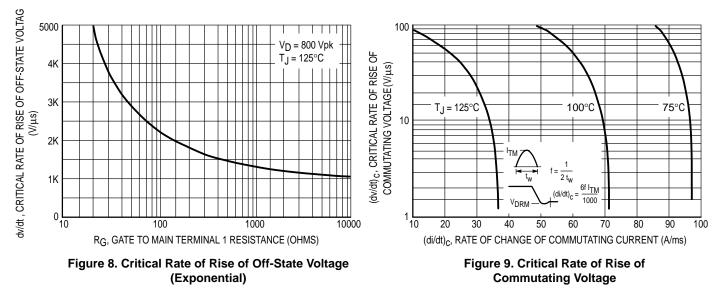
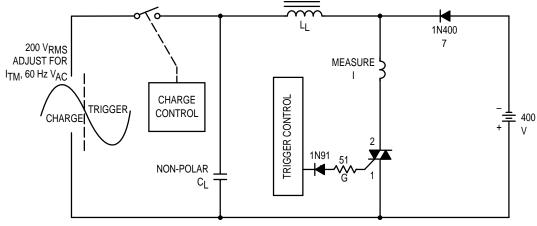


Figure 2. On-State Power Dissipation



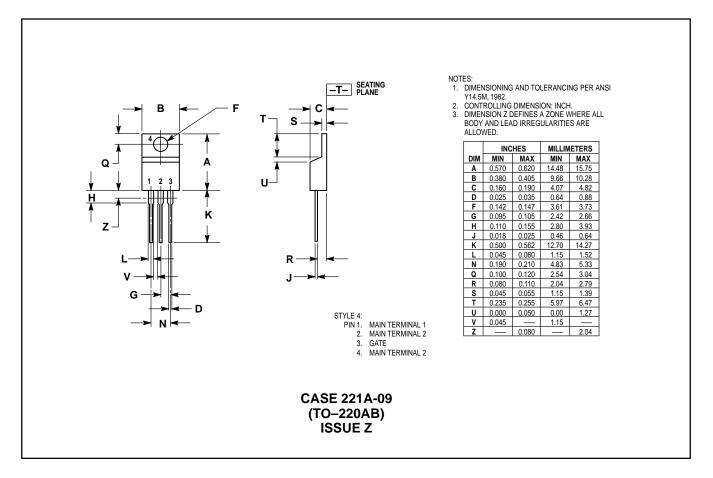




Note: Component values are for verification of rated (dv/dt)<sub>C</sub>. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Voltage

#### PACKAGE DIMENSIONS



# NOTES

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